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# Nonvolatile Memories 2

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**Table of Contents**

*Preface* *iii*

**Chapter 1**  
**Emerging Memories: Processes and Devices**

(Invited) Storage Class Memory and NAND Flash Memory Hybrid Solid-State Drives (SSD) 3  
*K. Takeuchi*

(Invited) Opportunities and Challenges of Atom Switch for Low-Power Programmable Logic 9  
*M. Tada, T. Sakamoto, H. Hada*

**Chapter 2**  
**ReRAM Characterization**

In Situ TEM Observation of Cu/MoO<sub>x</sub> ReRAM Switching 19  
*M. Kudo, Y. Ohno, K. Hamada, M. Arita, Y. Takahashi*

Temperature Dependence of Resistance in Conductive Filament Formed with Dielectric Breakdown of Ni/TiO<sub>2</sub>/Pt Structure 27  
*S. Otsuka, Y. Hamada, T. Shimizu, S. Shingubara*

Investigation of Thomson Effect in Cu/TaO<sub>x</sub>/Pt Resistive Switching Memory 33  
*T. Liu, T. Potnis, Y. Kang, S. El-Helw, M. Orlowski*

First-Principles Study of Oxygen Vacancy and Hydrogen Impurity Effects in the Pseudo-Hexagonal Ta<sub>2</sub>O<sub>5</sub> 41  
*J. Y. Kim, B. Magyari-Köpe, A. Haezghi, K. J. Lee, H. S. Kim, S. H. Lee, Y. Nishi*

### **Chapter 3**

#### **ReRAM Cells and Devices**

(Invited) Programmable Metallization Cells in Memory and Switching Applications <i>M. N. Kozicki, P. Dandamudi, H. J. Barnaby, Y. Gonzalez-Velo</i>	47
PN-Diode P-Oxide-Semiconductor/N-SiC/N-Si Resistive Nonvolatile Memory for Cross-Point Memory Array <i>Y. Sato, A. Yamashita, T. Tsukamoto, Y. Suda</i>	53
A CMOS Compatible, Forming Free TaO <sub>x</sub> ReRAM <i>A. J. Lohn, J. E. Stevens, P. R. Mickel, D. R. Hughart, M. J. Marinella</i>	59

### **Chapter 4**

#### **Flash Memory Characterization**

Effect of Intermetal Dielectric Layer On the Interpoly Dielectric Properties of Nonvolatile Memory Devices <i>J. Y. Ryoo, S. K. Sung, Y. S. Yim, J. E. Song, W. C. Shin, J. H. Song, D. H. Song, J. H. Choi, Y. Roh</i>	69
Impact of STI Gap-Fill Process Deposited by HDP-CVD in Flash Memory <i>H. S. Park, K. Y. Kim, O. C. Hong, H. S. Kim, H. Lee, K. P. Lee, I. S. Cho, B. D. Choi</i>	75
Low-Dielectric Constant SiCN Charge Trapping Layer for Nonvolatile Memory Applications <i>K. Kobayashi, S. Naito, S. Nakiri, Y. Ito</i>	81

### **Chapter 5**

#### **Flash Memory Devices**

(Invited) Improved Operation Characteristics in Charge-Trapping Flash Memory Devices with Engineered Dielectric Stack and SiGe Channel <i>Z. H. Ye, L. J. Liu, K. S. Chang-Liao</i>	93
--	----

Optimized Contact Engineering to Maximize Cell Current in NAND Flash Memory Technology	103
<i>J. H. Yoon, H. S. Kim, Y. S. Kim, J. K. Lee, E. S. Han, Y. Jeong, Y. I. Lee, S. J. Jang, H. G. Kim, S. W. Park, S. H. Park, H. B. Lee, K. P. Lee, I. S. Cho</i>	

CdSe Embedded ZrHfO Gate Dielectric Nonvolatile Memories – Charge Trapping and Breakdown Studies	109
<i>C. C. Lin, Y. Kuo</i>	

## **Chapter 6** **New Memories: STTRAM and PCRAM**

(Invited) Recent Developments in ST-MRAM, Including Scaling	117
<i>E. J. O'Sullivan, M. J. Gajek, J. J. Nowak, S. L. Brown, M. C. Gaidis, G. Hu, J. Z. Sun, P. L. Trouilloud, D. W. Abraham, R. P. Robertazzi, W. J. Gallagher, D. C. Worledge</i>	

Voltage-Induced Nonvolatile Change of Magnetic Anisotropy of CoFeB Ultrathin Films Stacked With Multivalent Oxides	127
<i>J. Koba, K. Kita</i>	

Special Electric Characteristics of Superlattice Phase Change Memory	135
<i>T. Ohyanagi, M. Kitamura, N. Takaura</i>	

Author Index	139
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